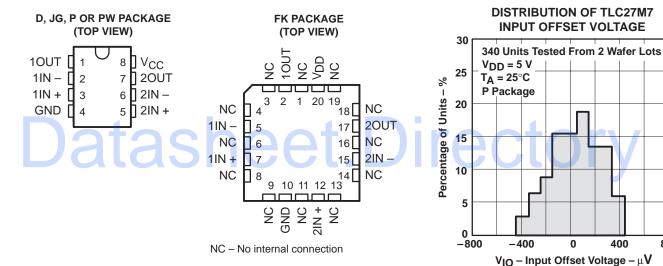
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- Trimmed Offset Voltage: TLC27M7 . . . 500 μV Max at 25°C, V_{DD} = 5 V
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over Specified Temperature Ranges: 0°C to 70°C ... 3 V to 16 V -40°C to 85°C ... 4 V to 16 V -55°C to 125°C ... 4 V to 16 V
- Single-Supply Operation
- Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix, I-Suffix Types)

- Low Noise . . . Typically 32 nV/√Hz at f = 1 kHz
- Low Power . . . Typically 2.1 mW at 25°C, V_{DD} = 5 V
- Output Voltage Range Includes Negative Rail
- High Input impedance . . . $10^{12} \Omega$ Typ
- ESD-Protection Circuitry
- Small-Outline Package Option Also Available in Tape and Reel
- Designed-In Latch-Up Immunity



AVAILABLE OPTIONS	

	Viemax			PACKAGE		
ТА	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)
	500 μV	TLC27M7CD	—	—	TLC27M7CP	—
0°C to 70°C	2 mV	TLC27M2BCD	—	—	TLC27M2BCP	—
00010700	5 mV	TLC27M2ACD	—	—	TLC27M2ACP	—
	10 mV	TLC27M2CD	—	—	TLC27M2CP	TLC27M2CPW
	500 μV	TLC27M7ID	—	—	TLC27M7IP	—
-40°C to 85°C	2 mV	TLC27M2BID	—	—	TLC27M2BIP	—
-40°C 10 85°C	5 mV	TLC27M2AID	—	—	TLC27M2AIP	—
	10 mV	TLC27M2ID	—	—	TLC27M2IP	TLC27M2IPW
-55°C to 125°C	500 μV	TLC27M7MD	TLC27M7MFK	TLC27M7MJG	TLC27M7MP	—
-55 0 10 125 0	10 mV	TLC27M2MD	TLC27M2MFK	TLC27M2MJG	TLC27M2MP	—

The D and PW package is available taped and reeled. Add R suffix to the device type (e.g., TLC27M7CDR).

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description

The TLC27M2 and TLC27M7 dual operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, low noise, and speeds approaching that of general-purpose bipolar devices. These devices use Texas Instruments silicon-gate LinCMOS technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, and high slew rates make these cost-effective devices ideal for applications which have previously been reserved for general-purpose bipolar products,but with only a fraction of the power consumption. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27M2 (10 mV) to the high-precision TLC27M7 (500 μ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

In general, many features associated with bipolar technology are available on LinCMOS[™] operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27M2 and TLC27M7. The devices also exhibit low voltage single-supply operation, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

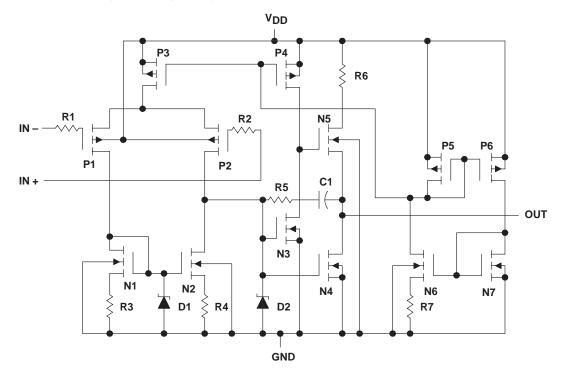
The device inputs and outputs are designed to withstand -100-mA surge currents without sustaining latch-up.

The TLC27M2 and TLC27M7 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in the degradation of the device parametric performance.

The C-suffix devices are characterized for operation from 0° C to 70° C. The I-suffix devices are characterized for operation from -40° C to 85° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.



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equivalent schematic (each amplifier)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V _{DD} (see Note 1) Differential input voltage, V _{ID} (see Note 2) Input voltage range, V _I (any input)	$\begin{array}{c} \dots & \pm V_{DD} \\ \dots & -0.3 \text{ V to } V_{DD} \end{array}$
Input current, I _I	±5 mA
Output current, I _O (each output)	
Total current into V _{DD}	45 mA
Total current out of GND	45 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	Unlimited
Continuous total dissipation	See Dissipation Rating Table
Continuous total dissipation	
Operating free-air temperature, T _A : C suffix	
Operating free-air temperature, T _A : C suffix I suffix	0°C to 70°C
Operating free-air temperature, T _A : C suffix I suffix M suffix	
Operating free-air temperature, T _A : C suffix I suffix	0°C to 70°C
Operating free-air temperature, T _A : C suffix I suffix M suffix Storage temperature range	0°C to 70°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.

2. Differential voltages are at IN+ with respect to IN-.

3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	
FK	1375 mW	11.0 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
Р	1000 mW	8.0 mW/°C	640 mW	520 mW	

recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SU	M SUFFIX	
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, VDD		3	16	4	16	4	16	V
	V _{DD} = 5 V		3.5	-0.2	3.5	0	3.5	V
Common-mode input voltage, V _{IC} V _{DD} = 10 V		-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	°C



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER	PARAMETER		DITIONS	т _А †	TL TL TL	.C27M2 .C27M2 .C27M2 .C27M2 .C27M7	AC BC C	
					2500	MIN	TYP	MAX	
		TLC27M2C	V _O = 1.4 V, R _S = 50 Ω,	V _{IC} = 0, R _I = 100 kΩ	25°C		1.1	10 12	
			-		Full range 25°C		0.9	5	mV
		TLC27M2AC	V _O = 1.4 V, R _S = 50 Ω,	V _{IC} = 0, R _I = 100 kΩ	Full range		0.9	6.5	
VIO	Input offset voltage		$V_0 = 1.4 V_{,}$	V _{IC} = 0,	25°C		220	2000	
		TLC27M2BC	$R_{S} = 50 \Omega,$	$V_{IC} = 0,$ $R_{I} = 100 \text{ k}\Omega$	Full range			3000	
			V _O = 1.4 V,	V _{IC} = 0,	25°C		185	500	μV
		TLC27M7C	$R_{S} = 50 \Omega,$	$R_{\rm I} = 100 \ \rm k\Omega$	Full range			1500	
αVIO	Average temperature c offset voltage	oefficient of input			25°C to 70°C		1.7		μV/°C
	-				25°C		0.1		
10	Input offset current (see	e Note 4)	V _O = 2.5 V,	$V_{IC} = 2.5 V$	70°C		7	300	рA
					25°C		0.6		
IВ	Input bias current (see	Note 4)	V _O = 2.5 V,	VIC = 2.5 V	70°C		40	600	рА
.,	Common-mode input v	oltage range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	0 0			Full range	-0.2 to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltag	je	V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	0°C	3	3.9		V
					70°C	3	4		
					25°C		0	50	
VOL	Low-level output voltag	e	$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
	Large-signal differentia	lvoltage			25°C	25	170		
AVD	amplification	i voltaye	$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 100 \text{ k}\Omega$	0°C	15	200		V/mV
	•		ļ		70°C	15	140		
					25°C	65	91		
CMRR	Common-mode rejection	on ratio	$V_{IC} = V_{ICR}min$		0°C	60	91		dB
					70°C	60	92		
	Supply-voltage rejectio	n ratio			25°C	70	93		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{DD} = 5 V \text{ to } 10 V,$	V _O = 1.4 V	0°C	60	92		dB
					70°C	60	94		
			V _O = 2.5 V,	V _{IC} = 2.5 V,	25°C		210	560	
IDD	Supply current (two am	plitiers)	No load		0°C		250	640	μA
					70°C		170	440	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	τ _A †	TL TL TL	C27M2	27M2AC 27M2BC 27M7C	
					25°C	MIN	TYP 1.1	MAX 10	
		TLC27M2C	V _O = 1.4 V, R _S = 50 Ω,	V _{IC} = 0, R _L = 100 kΩ	Full range		1.1	10	
			-	_	25°C		0.9	5	mV
		TLC27M2AC	V _O = 1.4 V, R _S = 50 Ω,	V _{IC} = 0, R _L = 100 kΩ	Full range		0.0	6.5	
VIO	Input offset voltage		V _O = 1.4 V,	VIC = 0,	25°C		224	2000	
		TLC27M2BC	$R_{S} = 50 \Omega,$	$R_L = 100 \text{ k}\Omega$	Full range			3000	.,
		TI 0071470	V _O = 1.4 V,	V _{IC} = 0,	25°C		190	800	μV
		TLC27M7C	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			1900	
ανιο	Average temperature co offset voltage	pefficient of input			25°C to 70°C		2.1		μV/°C
	lanut affact summark (as	Nete ()	N 5.V	N 5 M	25°C		0.1		- 0
IIO	Input offset current (see	e Note 4)	$V_{O} = 5 V,$	$V_{IC} = 5 V$	70°C		7	300	pА
lun	Input biog ourrept (acc	Note ()		$\mathcal{M} = \mathcal{F} \mathcal{M}$	25°C		0.7		۳Å
IВ	Input bias current (see	NOLE 4)	V _O = 5 V,	V _{IC} = 5 V	70°C		50	600	pА
	Common-mode input vo	oltage range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	-0.2 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltag	e	V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	0°C	7.8	8.7		V
					70°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage	е	$V_{ID} = -100 \text{ mV},$	IOT = 0	0°C		0	50	mV
					70°C		0	50	
	Large-signal differential	voltage			25°C	25	275		
AVD	amplification	vollage	$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 100 \text{ k}\Omega$	0°C	15	320		V/mV
			ļ		70°C	15	230		
					25°C	65	94		
CMRR	Common-mode rejection	n ratio	$V_{IC} = V_{ICR}min$		0°C	60	94		dB
					70°C	60	94		
	Supply-voltage rejection	n ratio			25°C	70	93		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$		$V_{DD} = 5 V \text{ to } 10 V,$	V _O = 1.4 V	0°C	60	92		dB
					70°C	60	94		
1	Current automatic titura		V _O = 5 V,	V _{IC} = 5 V,	25°C		285	600	
IDD	Supply current (two am	piiriers)	No load		0°C		345	800	μA
					70°C		220	560	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T _A †	TLC27M2I TLC27M2AI TLC27M2BI TLC27M7I			UNIT
						MIN	TYP	MAX	
		TLC27M2I	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		1.1	10	
			R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			13	mV
		TLC27M2AI	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		0.9	5	IIIV
VIO	Input offset voltage		R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			7	
۷IO	input onset voltage	TLC27M2BI	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		220	2000	
			R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			3500	μV
		TLC27M7I	V _O = 1.4 V,	$V_{IC} = 0,$	25°C		185	500	μv
		TEGZYIWIYI	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			2000	
αVIO	Average temperature con offset voltage	efficient of input			25°C to 85°C		1.7		μV/°C
					25°C		0.1		
10	Input offset current (see	Note 4)	V _O = 2.5 V,	V _{IC} = 2.5 V	85°C		24	1000	рА
					25°C		0.6		
IВ	Input bias current (see N	lote 4)	V _O = 2.5 V,	VIC = 2.5 V	85°C		200	2000	рА
	Common-mode input vo	tage range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	-0.2 to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage	9	V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	-40°C	3	3.9		V
					85°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	25	170		
AVD	Large-signal differential amplification	voltage	$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 100 \text{ k}\Omega$	-40°C	15	270		V/mV
	ampineation				85°C	15	130		
					25°C	65	91		
CMRR	Common-mode rejection	n ratio	$V_{IC} = V_{ICR}min$		−40°C	60	90		dB
					85°C	60	90		
					25°C	70	93		
^k SVR	Supply-voltage rejection (ΔVDD/ΔVIO)	ratio	$V_{DD} = 5 V \text{ to } 10 V,$	V _O = 1.4 V	-40°C	60	91		dB
					85°C	60	94		
					25°C		210	560	
IDD	Supply current (two amp	lifiers)	$V_{O} = 2.5 V$, No load	V _{IC} = 2.5 V,	-40°C		315	800	μA
					85°C		160	400	

[†] Full range is –40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T _A †	ТІ ТІ	C27M2 C27M2 C27M2 C27M2 C27M7	AI BI	UNIT
						MIN	TYP	MAX	
			V _O = 1.4 V,	$V_{IC} = 0,$	25°C		1.1	10	
		TLC27M2I	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			13	
			V _O = 1.4 V,	$V_{IC} = 0,$	25°C		0.9	5	mV
\/	Innut offerst voltage	TLC27M2AI	R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			7	
VIO	Input offset voltage	TLC27M2BI	V _O = 1.4 V,	VIC = 0,	25°C		224	2000	
			R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			3500	μV
		TLC27M7I	V _O = 1.4 V,	V _{IC} = 0,	25°C		190	800	μν
			R _S = 50 Ω,	RL = 100 kΩ	Full range			2900	
αNO	Average temperature coe offset voltage	efficient of input			25°C to 85°C		2.1		μV/°C
		(J-(- 4))		N(5)(25°C		0.1		
10	Input offset current (see I	Note 4)	V _O = 5 V,	$V_{IC} = 5 V$	85°C		26	1000	рA
					25°C		0.7		
IIB	Input bias current (see No	ote 4)	V _O = 5 V,	$V_{IC} = 5 V$	85°C		220	200 0	pА
.,	Common-mode input volt	age range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	0			Full range	-0.2 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	-40°C	7.8	8.7		V
					85°C	7.8	8.7		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	IOT = 0	-40°C		0	50	mV
					85°C		0	50	
					25°C	25	275		
AVD	Large-signal differential v amplification	oltage	$V_{O} = 1 V \text{ to } 6 V,$	$R_L = 100 \text{ k}\Omega$	-40°C	15	390		V/mV
					85°C	15	220		
					25°C	65	94		
CMRR	Common-mode rejection	ratio	$V_{IC} = V_{ICR}min$		-40°C	60	93		dB
					85°C	60	94		
	0 1 1 1 1				25°C	70	93		
^k SVR	Supply-voltage rejection (ΔVDD/ΔVIO)	ratio	$V_{DD} = 5 V \text{ to } 10 V,$	V _O = 1.4 V	-40°C	60	91		dB
					85°C	60	94		
					25°C		285	600	
IDD	Supply current		$V_{O} = 5 V$, No load	$V_{IC} = 5 V,$	-40°C		450	900	μA
					85°C		205	520	

[†]Full range is –40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	τ _A †		C27M2		UNIT
						MIN	TYP	MAX	
		TLC27M2M	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
VIO	Input offset voltage		R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
VIO	input onset voltage	TLC27M7M	V _O = 1.4 V,	V _{IC} = 0,	25°C		185	500	IIIV
			R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			3750	
αVIO	Average temperature coeff offset voltage	icient of input			25°C to 125°C		1.7		μV/°C
l. e	Input offerst surrent (ass No	ato (1)			25°C		0.1		pА
10	Input offset current (see No	ne 4)	V _O = 2.5 V,	V _{IC} = 2.5 V	125°C		1.4	15	nA
	Input bias current (see Not	a 4)			25°C		0.6		pА
IΒ	input bias current (see Not	8 4)	V _O = 2.5 V,	V _{IC} = 2.5 V	125°C		9	35	nA
Vice	Common-mode input voltage range				25°C	0 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	0 to 3.5			V
					25°C	3.2	3.9		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	−55°C	3	3.9		V
					125°C	3	4		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	Leave she al differential and	1			25°C	25	170		
AVD	Large-signal differential vol amplification	tage	$V_{O} = 0.25 V \text{ to } 2 V,$	$R_L = 100 \text{ k}\Omega$	−55°C	15	290		V/m∖
	ampinoadon				125°C	15	120		
					25°C	65	91		
CMRR	Common-mode rejection ra	atio	$V_{IC} = V_{ICR}min$		−55°C	60	89		dB
					125°C	60	91		
	O male and the second section of	r -			25°C	70	93		
^k SVR	Supply-voltage rejection ra (ΔVDD/ΔVIO)	liu	$V_{DD} = 5 V \text{ to } 10 V,$	$V_{O} = 1.4 V$	−55°C	60	91		dB
					125°C	60	94		
			V _O = 2.5 V,	V _{IC} = 2.5 V,	25°C		210	560	
IDD	Supply current (two amplified	ers)	$v_{O} = 2.5 v$, No load	VIC = 2.5 V,	−55°C		340	880	μΑ
					125°C		140	360	

[†] Full range is –55°C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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electrical characteristics at specified free-air temperature, V_{DD} = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	т _А †		.C27M2M .C27M7M		UNIT
						MIN	TYP	MAX	
		TLC27M2M	V _O = 1.4 V,	VIC = 0,	25°C		1.1	10	
Via	Input offset voltage		R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			12	mV
VIO	input onset voltage	TLC27M7M	V _O = 1.4 V,	V _{IC} = 0,	25°C		190	800	IIIV
			R _S = 50 Ω,	$R_L = 100 \text{ k}\Omega$	Full range			4300	
αγιο	Average temperature coeffic offset voltage	ient of input			25°C to 125°C		2.1		μV/°C
li o	Input offset current (see Not	o 1)	V _O = 5 V,	VIC = 5 V	25°C		0.1		٣Å
IIO	input onset current (see Not	e 4)	$v_{\rm O} = 5 v$,	AIC = 2 A	125°C		1.8	15	pА
lup	Input bias current (see Note	4)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.7		n۸
IΒ		<i>۲)</i>	v 0 = 5 v,	VIC = 5 V	125°C		10	35	pА
\/	Common-mode input voltage range				25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	-			Full range	0 to 8.5			V
					25°C	8	8.7		
Vон	High-level output voltage		V _{ID} = 100 mV,	$R_L = 100 \text{ k}\Omega$	−55°C	7.8	8.6		V
					125°C	7.8	8.8		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	Lanna alterativitte essettativati				25°C	25	275		
AVD	Large-signal differential volta amplification	age	$V_{O} = 1 V \text{ to } 6 V,$	R_L = 100 k Ω	−55°C	15	420		V/mV
					125°C	15	190		
					25°C	65	94		
CMRR	Common-mode rejection rat	io	$V_{IC} = V_{ICR}min$		−55°C	60	93		dB
					125°C	60	93		
	Supply-voltage rejection rati	0			25°C	70	93		
^k SVR	$(\Delta V_{DD}/\Delta V_{IO})$	0	$V_{DD} = 5 V \text{ to } 10 V,$	$V_{O} = 1.4 V$	−55°C	60	91		dB
	,				125°C	60	94		
			V _O = 5 V,	V _{IC} = 5 V,	25°C		285	600	
IDD	Supply current (two amplifie	rs)	No load	· ic - • •,	−55°C		490	1000	μA
					125°C		180	480	

[†] Full range is -55° C to 125° C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



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	PARAMETER		TEST CONDITIONS			TLC27M2C TLC27M2AC TLC27M2BC TLC27M7C MIN TYP MAX		
				25°C		0.43		
			VI(PP) = 1 V	0°C		0.46		1
00		$R_{L} = 100 \text{ k}\Omega,$		70°C		0.36		
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
			V _{I(PP)} = 2.5 V	0°C	0.43		1	
				70°C		0.34		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz
				25°C		55		
Вом	Maximum output-swing bandwidth	V _O = V _{OH} , R _L = 100 kΩ,	CL = 20 pF, See Figure 1	0°C		60		kHz
		TYL = 100 K32,	Oce rigure r	70°C		50		1
			0 00 5	25°C		525		
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	0°C		600		kHz
		Geo Figure 0		70°C		400		
		10 m)/	4 D	25°C		40°		
φm	Phase margin	V _I = 10 mV, C _L = 20 pF,	f = B ₁ , See Figure 3	0°C		41°		
				70°C		39°		

operating characteristics at specified free-air temperature, V_{DD} = 5 V

operating characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V

	PARAMETER		TEST CONDITIONS			TLC27M2C TLC27M2AC TLC27M2BC TLC27M7C		
						TYP	MAX	
				25°C		0.62		
			VI(PP) = 1 V	0°C		0.67		
SR		$R_{L} = 100 \text{ k}\Omega,$		70°C		0.51		V/μs
	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.56		v/µs
			VI(PP) = 5.5 V	0°C		0.61		
				70°C		0.46		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√ Hz
				25°C		35		
ВОМ	Maximum output-swing bandwidth	V _O = V _{OH} , R _L = 100 kΩ,	C _L = 20 pF, See Figure 1	0°C		40		kHz
		NC - 100 K32,	Geerigure i	70°C		30		
				25°C		635		
B ₁	Unity-gain bandwidth	VI = 10 mV, See Figure 3	C _L = 20 pF,	0°C		710		kHz
		See Figure 5		70°C		510		
				25°C		43°		
∮m	Phase margin	V _I = 10 mV, C _L = 20 pF,	f = B ₁ , See Figure 3	0°C		44°		
			oce i igure o	70°C		42°		1



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operating characteristics at specified free-air temperature, V_{DD} = 5 V

	PARAMETER	TEST CO	ONDITIONS	TA	TLC27M2I TLC27M2AI TLC27M2BI TLC27M7I MIN TYP MAX			UNIT	
			1	25°C		0.43			
	Slew rate at unity gain	$R_L = 100 kΩ,$ $C_L = 20 pF,$ See Figure 1	V _{I(PP)} = 1 V	−40°C		0.51			
			,	85°C		0.35		V/µs	
SR				25°C		0.40			
			V _{I(PP)} = 2.5 V	−40°C		0.48	0.48		
				85°C		0.32			
V _n	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz	
				25°C		55			
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH},$ $R_I = 100 \text{ k}\Omega,$	C _L = 20 pF, See Figure 1	-40°C		75		kHz	
		NC = 100 N32,	Oce rigure r	85°C		45			
		N 40 M	0 00 5	25°C		525			
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	-40°C		770		MHz	
		occ riguie o		85°C		370			
		$1/1 = 10 m^{1/2}$	f _ D .	25°C		40°			
φm	Phase margin	V _I = 10 mV, C _L = 20 pF,	f = B ₁ , See Figure 3	−40°C		43°]	
		L - p ,	- 5	85°C		38°			

operating characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 10 V

PARAMETER		TEST CO	ONDITIONS	TA	TLC27M2I TLC27M2AI TLC27M2BI TLC27M7I		UNIT	
						TYP		MAX
				25°C		0.62		
			VI(PP) = 1 V	-40°C		0.77		
SP	SR Slew rate at unity gain	$R_{L} = 100 \text{ k}\Omega$,		85°C		0.47		Mug
		C _L = 20 pF, See Figure 1		25°C		0.56		V/μs
			V _{I(PP)} = 5.5 V	-40°C		0.70		
				85°C		0.44		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√ Hz
				25°C		35		
Вом	Maximum output-swing bandwidth	V _O = V _{OH} , R _L = 100 kΩ,	C _L = 20 pF, See Figure 1	-40°C		45		kHz
		KL = 100 K32,	Gee l'igure i	85°C		25		
				25°C		635		
B ₁	Unity-gain bandwidth	VI = 10 mV, See Figure 3	C _L = 20 pF,	-40°C		880		MHz
		See Figure 3		85°C		480		
				25°C		43°		
∮m	Phase margin	VI = 10 mV, CL = 20 pF,	f = B ₁ , See Figure 3	-40°C		46°		
		0L - 20 pr,	cco riguio o	85°C		41°		



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	PARAMETER	TEST CO	ONDITIONS	тд	TLC27M2M TLC27M7M			UNIT
				MIN TYP MAX				
				25°C		0.43		
			VI(PP) = 1 V	−55°C	0.54			
SR	Clow rate at unity gain	$R_L = 100 k\Omega$,		125°C		0.29		
SK	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.40		V/μs
		Ŭ	V _{I(PP)} = 2.5 V	−55°C		0.49		
				125°C		0.28		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz
		V _O = V _{OH} , R _L = 100 kΩ,		25°C		55		kHz
Вом	Maximum output-swing bandwidth		$C_L = 20 \text{ pF},$	−55°C		80		
			See l'igule i	125°C		40		
				25°C		525		
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	C _L = 20 pF,	−55°C		850		kHz
		Jose rigule 3		125°C		330]
[¢] m		10 - 10	()	25°C		40°		
	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−55°C		44°		1
		- 20 pl,	2001 19010 0	125°C		36°]

operating characteristics at specified free-air temperature, V_{DD} = 5 V

operating characteristics at specified free-air temperature, V_{DD} = 10 V

	PARAMETER	TEST CO	ONDITIONS	TA	TLC27M2M TLC27M7M			UNIT	
					MIN	TYP	MAX		
				25°C		0.62			
	Slew rate at unity gain		VI(PP) = 1 V	−55°C		0.81			
SR		$R_{L} = 100 k\Omega,$ $C_{L} = 20 pF,$		125°C		0.38)//uo	
		See Figure 1		25°C		0.56		V/μs	
			V _{I(PP)} = 5.5 V	−55°C		0.73			
				125°C		0.35			
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	R _S = 20 Ω,	25°C		32		nV/√Hz	
		$V_{O} = V_{OH},$ $R_{L} = 100 \text{ k}\Omega,$		25°C		35		kHz	
ВОМ	Maximum output-swing bandwidth			−55°C		50			
			See lighte l	125°C		20			
				25°C		635			
B ₁	Unity gain bandwidth	V _I = 10 mV, See Figure 3	CL = 20 pF,	−55°C		960		kHz	
		See rigure 5		125°C		440			
		10 m)/	<u> </u>	25°C		43°			
∮m	Phase margin	$V_{I} = 10 \text{ mV},$	t = B ₁ , See Figure 3	−55°C		47°			
		0 <u> </u>	eee rigule o	125°C		39°			

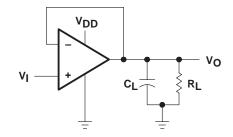


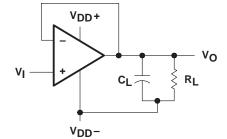
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PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC27M2 and TLC27M7 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

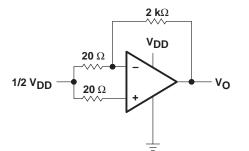


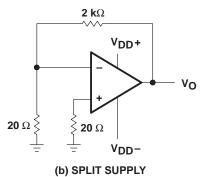


(b) SPLIT SUPPLY

(a) SINGLE SUPPLY

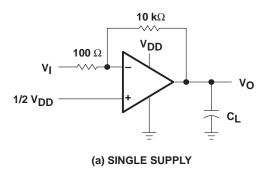


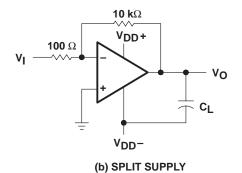


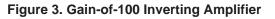


(a) SINGLE SUPPLY











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PARAMETER MEASUREMENT INFORMATION

input bias current

Because of the high input impedance of the TLC27M2 and TLC27M7 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- 2. Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution—many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

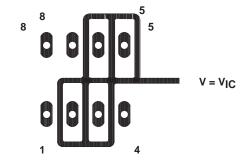


Figure 4. Isolation Metal Around Device Inputs (JG and P packages)

low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figures 14 through 19 in the Typical Characteristics of this data sheet.



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PARAMETER MEASUREMENT INFORMATION

input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage, since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.

full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.

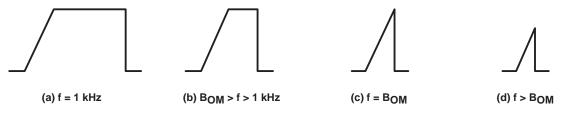


Figure 5. Full-Power-Response Output Signal

test time

Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.



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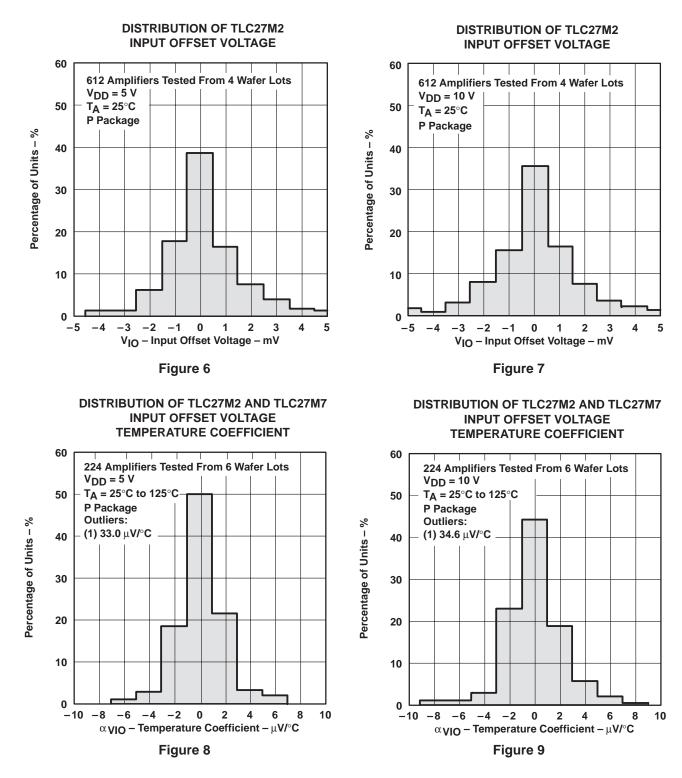
TYPICAL CHARACTERISTICS

			FIGURE
VIO	Input offset voltage	Distribution	6, 7
αVIO	Temperature coefficient	Distribution	8, 9
VOH	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V _{OL}	Low-level output voltage	vs Common-mode input voltage vs Differential input voltage vs Free-air temperature vs Low-level output current	14, 15 16 17 18, 19
AVD	Differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
IIB/IIO	Input bias and input offset current	vs Free-air temperature	22
VIC	Common-mode input voltage	vs Supply voltage	23
IDD	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
VO(PP)	Maximum peak-to-peak output voltage	vs Frequency	29
B ₁	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
[¢] m	Phase margin	vs Supply voltage vs Free-air temperature vs Capacitive loads	34 35 36
V _n	Equivalent input noise voltage	vs Frequency	37
¢	Phase shift	vs Frequency	32, 33

Table of Graphs



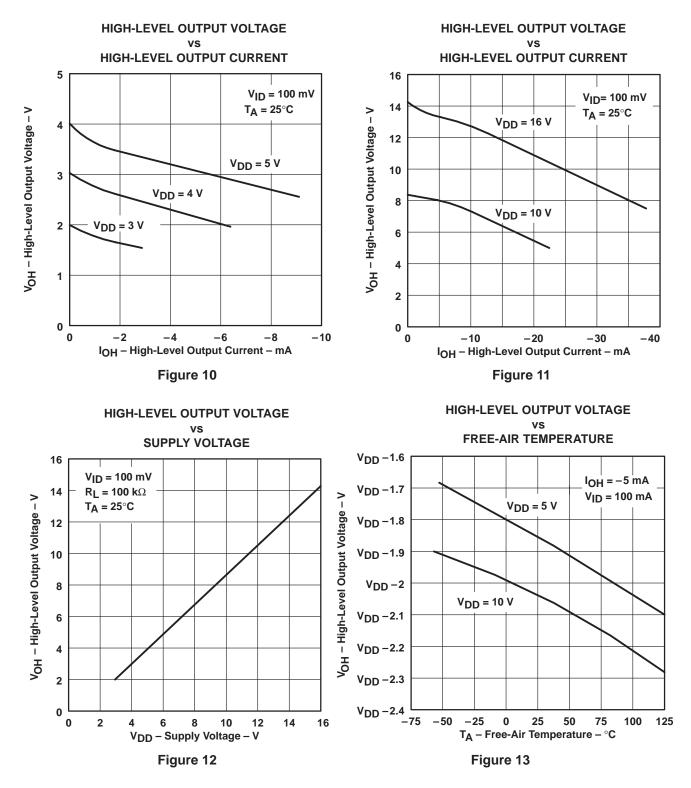
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TYPICAL CHARACTERISTICS



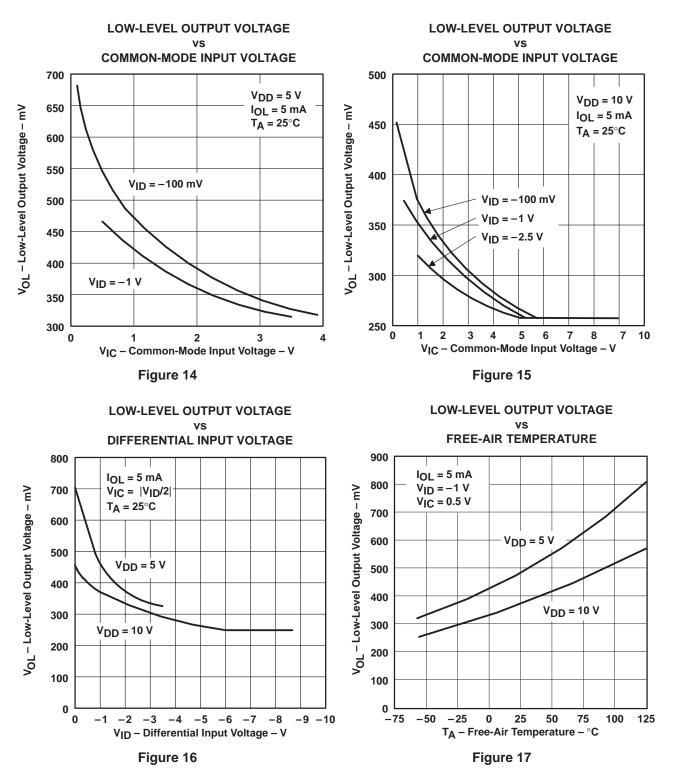
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TYPICAL CHARACTERISTICS[†]



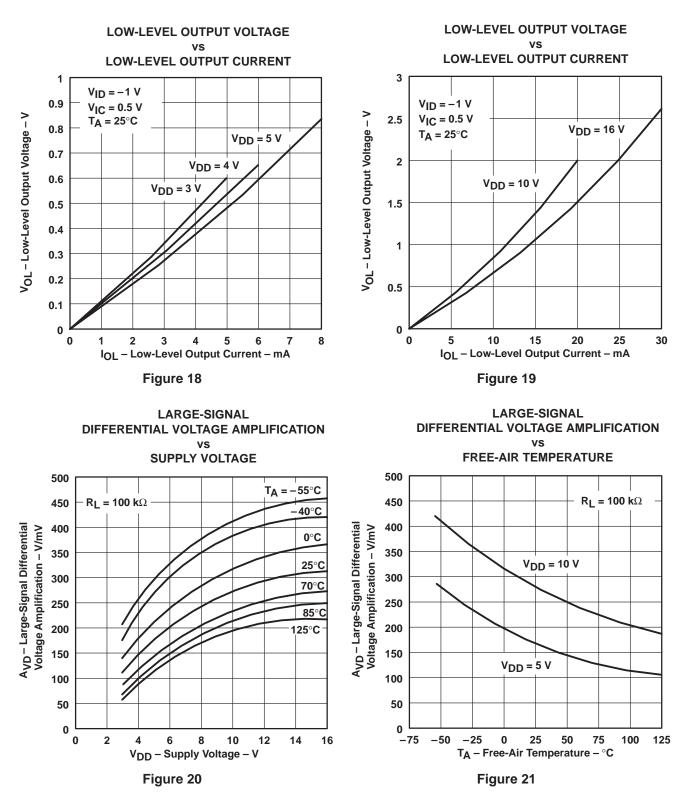
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TYPICAL CHARACTERISTICS[†]



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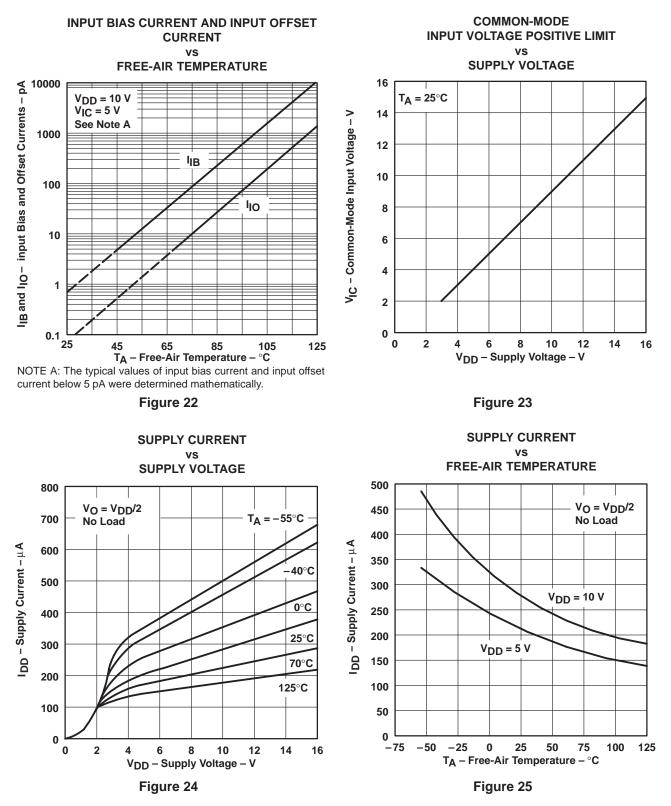


TYPICAL CHARACTERISTICS[†]



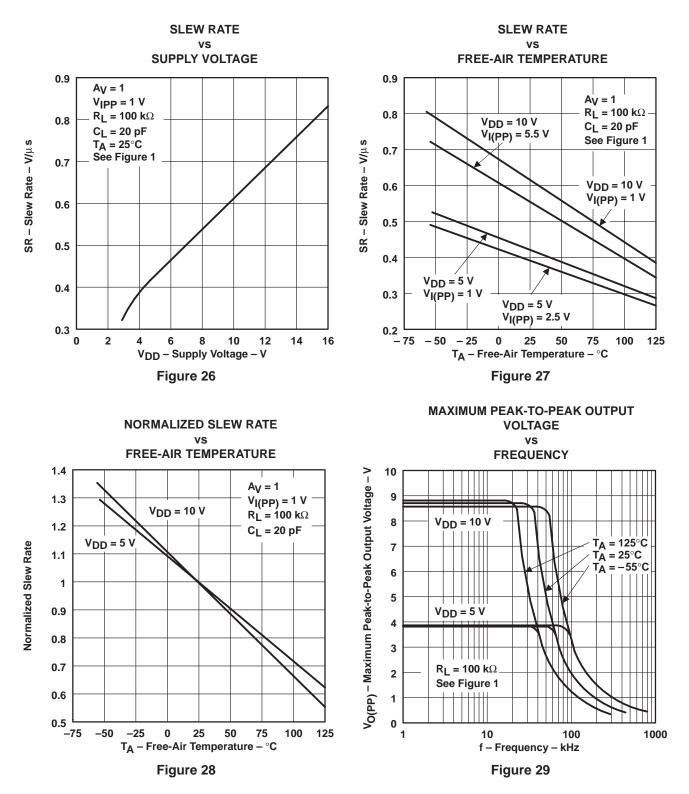
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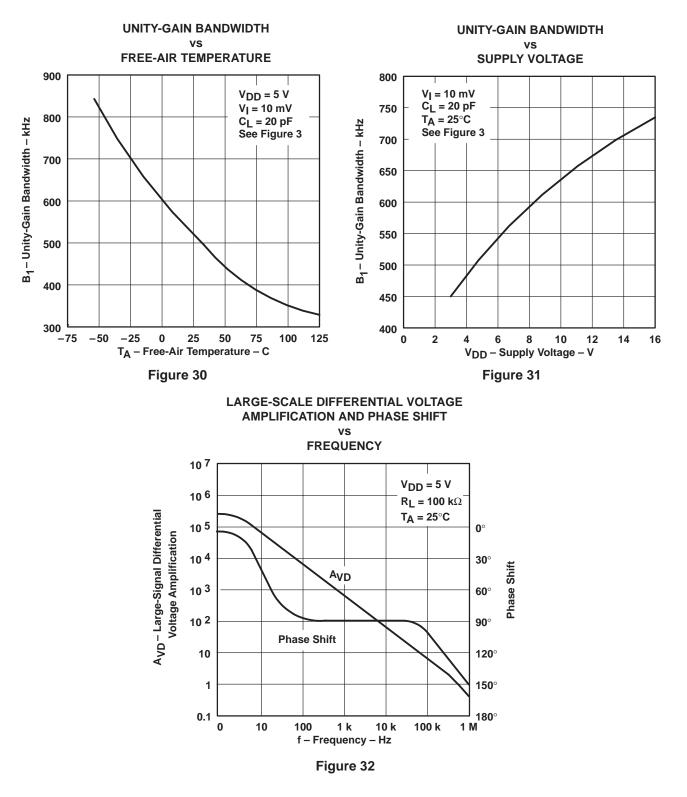
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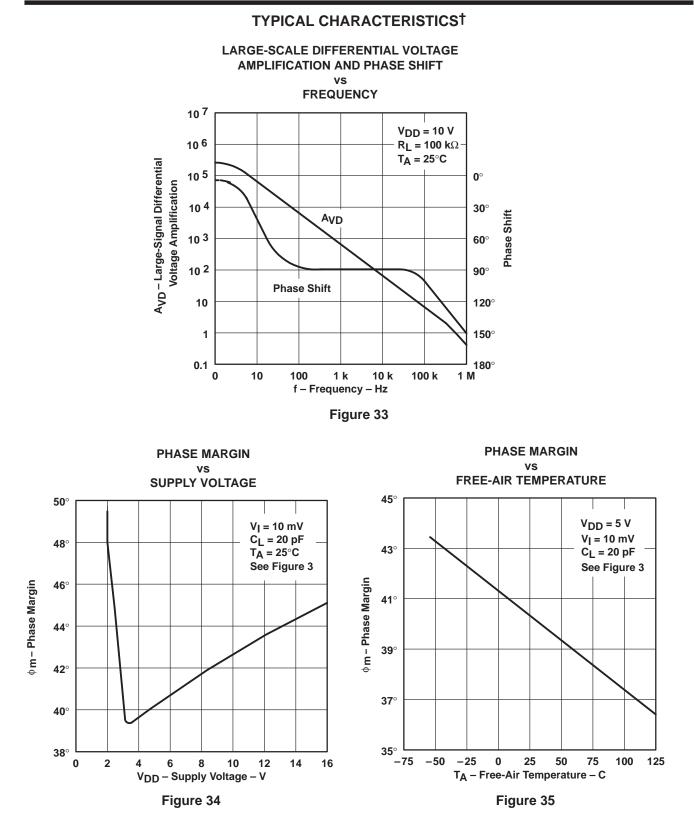
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TYPICAL CHARACTERISTICS[†]

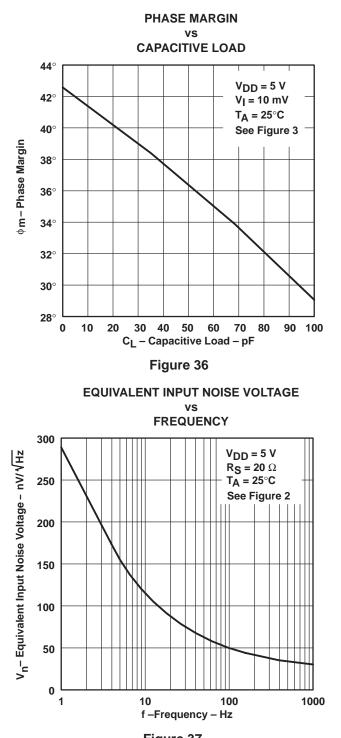


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TYPICAL CHARACTERISTICS





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APPLICATION INFORMATION

single-supply operation

While the TLC27M2 and TLC27M7 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27M2 and TLC27M7 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27M2 and TLC27M7 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- 1. Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

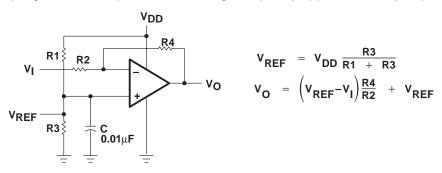
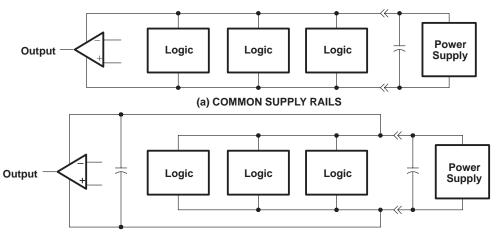


Figure 38. Inverting Amplifier With Voltage Reference



(b) SEPARATE BYPASSED SUPPLY RAILS (preferred)

Figure 39. Common Versus Separate Supply Rails



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APPLICATION INFORMATION

input characteristics

The TLC27M2 and TLC27M7 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at $V_{DD} - 1$ V at $T_A = 25^{\circ}$ C and at $V_{DD} - 1.5$ V at all other temperatures.

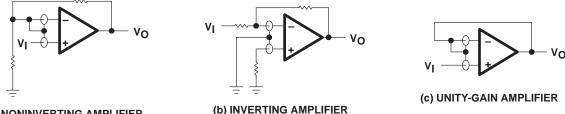
The use of the polysilicon-gate process and the careful input circuit design gives the TLC27M2 and TLC27M7 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1μ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27M2 and TLC27M7 are well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27M2 and TLC27M7 result in a very low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than 50 k Ω , since bipolar devices exhibit greater noise currents.



(a) NONINVERTING AMPLIFIER

Figure 40. Guard-Ring Schemes

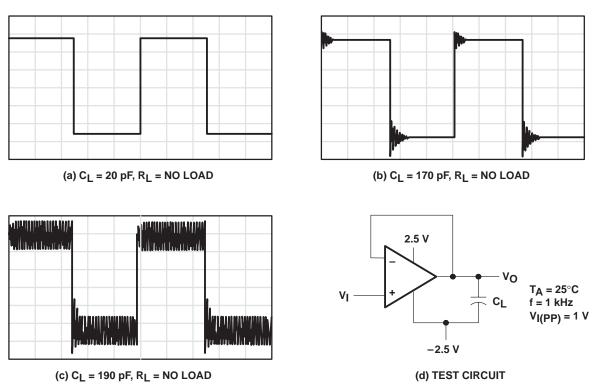
output characteristics

The output stage of the TLC27M2 and TLC27M7 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

All operating characteristics of the TLC27M2 and TLC27M7 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.



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APPLICATION INFORMATION



output characteristics (continued)

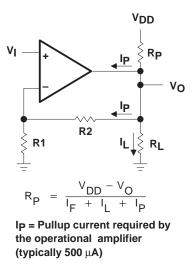
Although the TLC27M2 and TLC27M7 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R_P) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately 60Ω and 180Ω , depending on how hard the op amp input is driven. With very low values of R_P , a voltage offset from 0 V at the output occurs. Second, pullup resistor R_P acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.



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APPLICATION INFORMATION

output characteristics (continued)





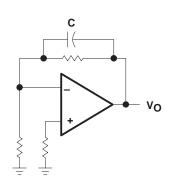


Figure 43. Compensation for Input Capacitance

feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

electrostatic-discharge protection

The TLC27M2 and TLC27M7 incorporate an internal electrostatic-discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

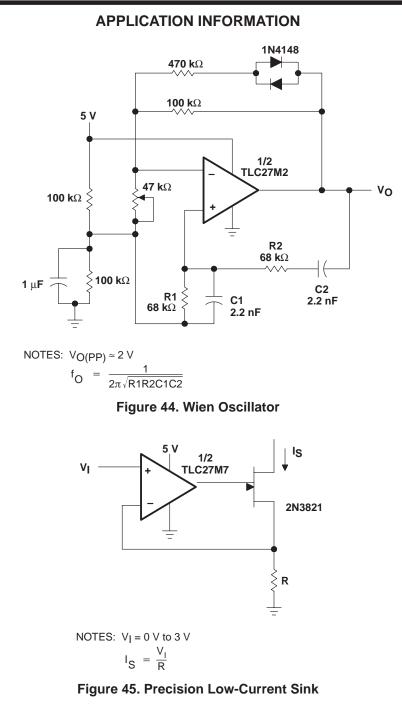
latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27M2 and TLC27M7 inputs and outputs were designed to withstand –100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

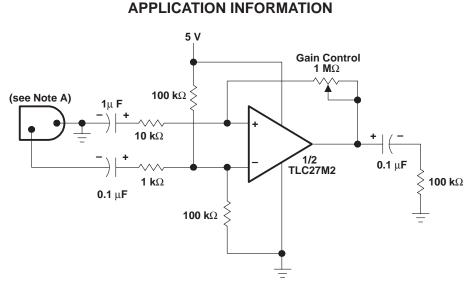


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NOTE A: Low to medium impedance dynamic mike



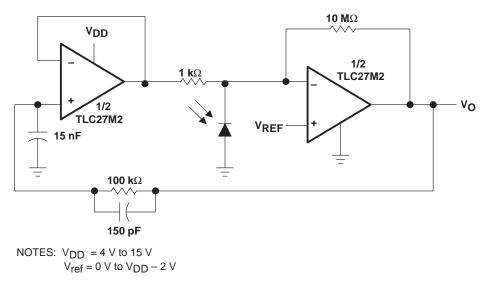


Figure 47. Photo-Diode Amplifier With Ambient Light Rejection



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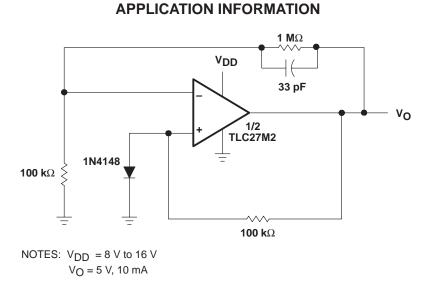


Figure 48. 5-V Low-Power Voltage Regulator

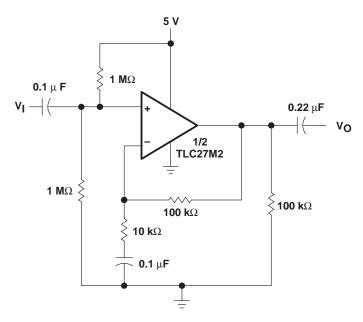


Figure 49. Single-Rail AC Amplifiers



TEXAS INSTRUMENTS www.ti.com

11-Dec-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLC27M2ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2ACPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2AIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2AIPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BCPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2BIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2BIPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

PACKAGE OPTION ADDENDUM

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Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TLC27M2CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2CPSLE	OBSOLETE	SO	PS	8		TBD	Call TI	Call TI
TLC27M2CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI
TLC27M2CPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2CPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M2IPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M2MD	ACTIVE	SOIC	D	8	75	TBD	CU NIPDAU	Level-1-220C-UNLIM
TLC27M2MDR	ACTIVE	SOIC	D	8		TBD	Call TI	Call TI
TLC27M2MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLC27M2MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLC27M2MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLC27M7CD	ACTIVE	SOIC	D	8	75	Green (RoHS &	CU NIPDAU	Level-1-260C-UNLIN

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
						no Sb/Br)		
TLC27M7CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLC27M7IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLC27M7MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLC27M7MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLC27M7MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLC27M7MUB	OBSOLETE	CFP	U	10	_	TBD	Call TI	Call TI

⁽¹⁾ The marketing status values are defined as follows:

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⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



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MECHANICAL DATA

MCER001A - JANUARY 1995 - REVISED JANUARY 1997



CERAMIC DUAL-IN-LINE



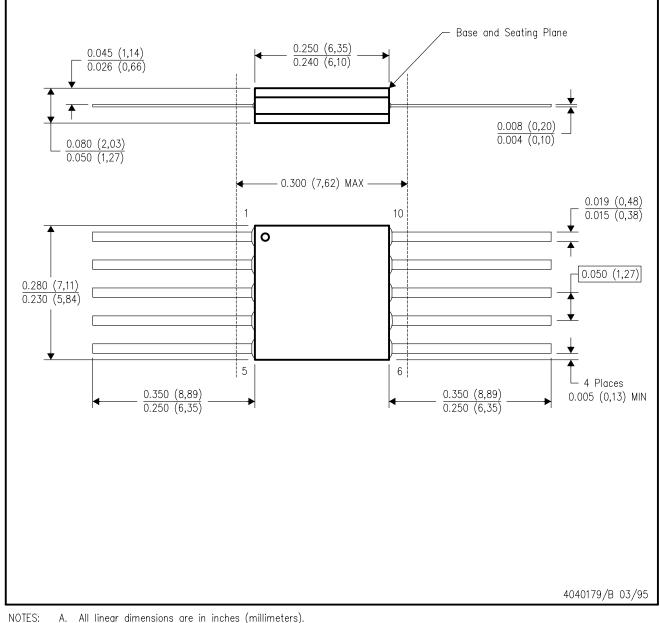
NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8



U (S-GDFP-F10)

CERAMIC DUAL FLATPACK



- Α. All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice. Β.
 - This package can be hermetically sealed with a ceramic lid using glass frit. C.
 - D. Index point is provided on cap for terminal identification only.
 - E. Falls within MIL STD 1835 GDFP1-F10 and JEDEC MO-092AA



MLCC006B - OCTOBER 1996

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. The terminals are gold plated.
- E. Falls within JEDEC MS-004



MECHANICAL DATA

MPDI001A - JANUARY 1995 - REVISED JUNE 1999



- NOTES: A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Falls within JEDEC MS-001

For the latest package information, go to http://www.ti.com/sc/docs/package/pkg_info.htm



D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.

Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.

E. Reference JEDEC MS-012 variation AA.



MECHANICAL DATA

PS (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



MECHANICAL DATA

MTSS001C - JANUARY 1995 - REVISED FEBRUARY 1999

PW (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153



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